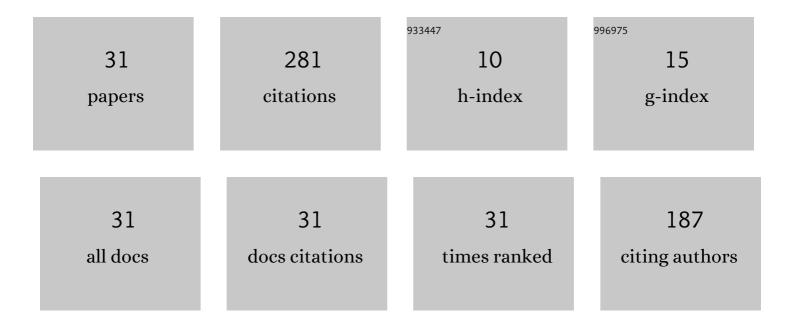
Makbule Terlemezoglu

List of Publications by Year in descending order

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#	Article	lF	CITATIONS
1	Growth and optical characterization of Sn0.6Sb0.4Se layer single crystals for optoelectronic applications. Materials Science in Semiconductor Processing, 2022, 141, 106434.	4.0	4
2	Temperature-dependent optical characteristics of sputtered NiO thin films. Applied Physics A: Materials Science and Processing, 2022, 128, 1.	2.3	11
3	Optical and structural characteristics of electrodeposited Cd 1-xZnxS nanostructured thin films. Optical Materials, 2021, 114, 110966.	3.6	7
4	Structural and temperature-tuned bandgap characteristics of thermally evaporated β-In2S3 thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 15851-15856.	2.2	6
5	A Study on Tetragonal-star Like Shaped Inverted Pyramid Texturing. , 2021, , .		0
6	Illumination and voltage effects on the forward and reverse bias current–voltage (I-V) characteristics in In/In2S3/p-Si photodiodes. Journal of Materials Science: Materials in Electronics, 2021, 32, 21825-21836.	2.2	21
7	The effect of Zn concentration on the structural and optical properties of Cd1-xZnxS nanostructured thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 25225-25233.	2.2	2
8	Fabrication of CdSexTe1-x thin films by sequential growth using double sources. Physica B: Condensed Matter, 2021, 619, 413232.	2.7	2
9	Characterization of Cu-rich and Zn-poor Cu2ZnSnS4 single crystal grown by vertical Bridgman technique. Journal of Crystal Growth, 2021, 574, 126336.	1.5	3
10	Vibrational modes in (TlGaS2)x‒(TlGaSe2)1â^'x mixed crystals by Raman measurements: compositional dependence of the mode frequencies and line-shapes. Journal of Materials Science: Materials in Electronics, 2020, 31, 14330-14335.	2.2	6
11	Electrical characterization of CdZnTe/Si diode structure. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	9
12	Material and Si-based diode analyses of sputtered ZnTe thin films. Journal of Materials Science: Materials in Electronics, 2020, 31, 11390-11397.	2.2	5
13	Temperature-tuned band gap properties of MoS2 thin films. Materials Letters, 2020, 275, 128080.	2.6	20
14	Investigation of band gap energy versus temperature for SnS2 thin films grown by RF-magnetron sputtering. Physica B: Condensed Matter, 2020, 591, 412264.	2.7	8
15	Temperature-dependent material characterization of CuZnSe2 thin films. Thin Solid Films, 2020, 701, 137941.	1.8	3
16	Temperature dependent band gap in SnS2xSe(2-2x) (x = 0.5) thin films. Materials Science in Semiconductor Processing, 2020, 114, 105083.	4.0	7
17	Investigation of electrical characteristics of Ag/ZnO/Si sandwich structure. Journal of Materials Science: Materials in Electronics, 2019, 30, 15371-15378.	2.2	12
18	Determination of current transport characteristics in Au-Cu/CuO/n-Si Schottky diodes. Physica B: Condensed Matter, 2019, 570, 246-253.	2.7	20

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#	Article	IF	CITATIONS
19	Characterization of one-step deposited Cu2ZnSnS4 thin films derived from a single crystalline powder. Renewable Energy, 2019, 143, 1133-1142.	8.9	19
20	CZTSSe thin films fabricated by single step deposition for superstrate solar cell applications. Journal of Materials Science: Materials in Electronics, 2019, 30, 11301-11306.	2.2	8
21	Frequency effect on electrical and dielectric characteristics of In/Cu2ZnSnTe4/Si/Ag diode structure. Journal of Materials Science: Materials in Electronics, 2019, 30, 9814-9821.	2.2	11
22	Temperature dependence of band gaps in sputtered SnSe thin films. Journal of Physics and Chemistry of Solids, 2019, 131, 22-26.	4.0	18
23	Temperature dependence of electrical properties in \$\$hbox {In/Cu}_{{2}hbox {ZnSnTe}_{{4}hbox {/Si/Ag diodes}\$\$ In/Cu 2 ZnSnTe 4 /Si/Ag diodes. Bulletin of Materials Science, 2019, 42, 1.	1.7	13
24	Construction of self-assembled vertical nanoflakes on CZTSSe thin films. Materials Research Express, 2019, 6, 026421.	1.6	8
25	Transfer of ordered and disordered Si nanowires onto alien substrates for the fabrication of third-generation solar cells. , 2019, , .		0
26	Analysis of current conduction mechanism in CZTSSe/n-Si structure. Journal of Materials Science: Materials in Electronics, 2018, 29, 5264-5274.	2.2	20
27	Investigation of carrier transport mechanisms in the Cu–Zn–Se based hetero-structure grown by sputtering technique. Canadian Journal of Physics, 2018, 96, 816-825.	1.1	10
28	Deposition of CZTSe thin films and illumination effects on the device properties of Ag/n-Si/p-CZTSe/In heterostructure. Journal of Alloys and Compounds, 2017, 709, 337-343.	5.5	16
29	Investigation of precursor sequence and post-annealing effects on the properties of Cu ₂ SnZnSe ₄ thin films deposited by the elemental thermal evaporation. Materials Research Express, 2017, 4, 086411.	1.6	12
30	Growth and Characterization of Stoichiometric Cu 2 ZnSnS 4 Crystal Using Vertical Bridgman Technique. Physica Status Solidi (A) Applications and Materials Science, 0, , .	1.8	0
31	A Study on the Structural, Morphological and Optical Properties of Cu2-xse Thin Films Deposited by Thermal Evaporation, Bilecik Åževh Edebali Äœniversitesi Fen Bilimleri Dergisi, O	0.6	0